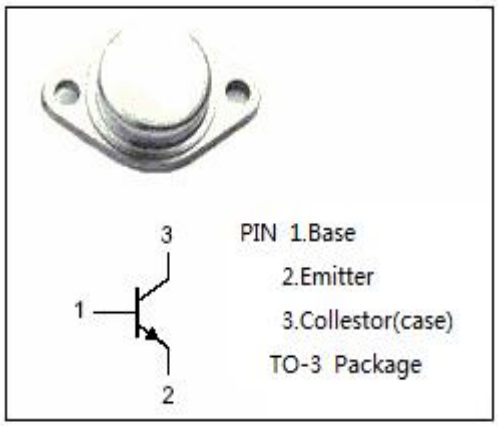
isc Silicon NPN Power Transistors — BU112

DESCRIPTION

- Collector-Emitter Voltage-
  :$V_{CEX(SUS)}$ = 550V(Min.)
- Collector Current- I_C= 10A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

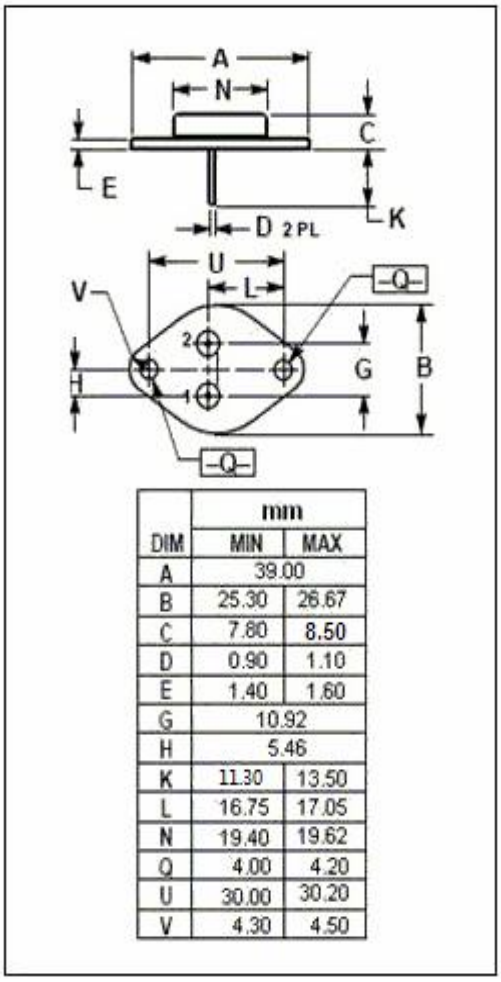


APPLICATIONS

- Designed for deflection circuits applications in color TV receivers fitted with 90℃ kinescope.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Emitter Voltage	550	V
V_{CEX}	Collector-Emitter Voltage V_{BE}= -5V	550	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	10	A
I_B	Base Current-Continuous	4	A
P_C	Collector Power Dissipation @T_C=25℃	60	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.9	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Collector-Base Breakdown Voltage	I_E= 30mA; I_C= 0	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 2A			3.0	V
I_{CEX}	Collector Cutoff Current	V_{CE}= 550V; V_{BE}= -5V			10	mA
h_{FE}	DC Current Gain	I_C= 6A; V_{CE}= 2V	7			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 4V		6		MHz
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1MHz		250		pF
t_f	Fall Time	I_C=6A; I_{B1}= 1A; V_{BE}= -3V			1.0	μs